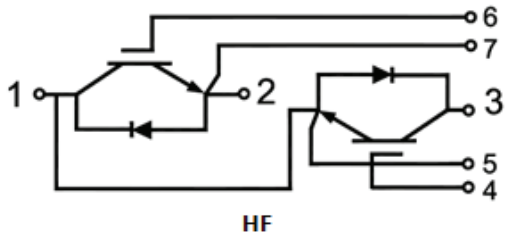
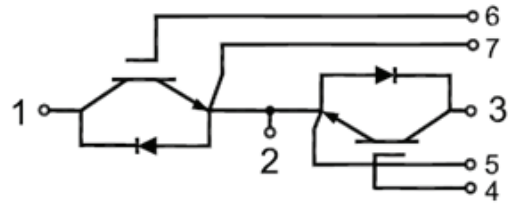
GT450HF120T2NH
GT450CE120T2NH
IGBT Module

Features：

- Trench & Field Stop IGBT
- Short Circuit Rated>10μs
- Low Switching Loss
- 100% RBSOA Tested(2×Ic)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



HF



CE

Applications：

- Welding
- HEV Inverter
- Industrial Motor Drives
- UPS

IGBT, Inverter
Maximum Rated Values

V_{CES}	Collector-Emitter Blocking Voltage	T_J=25℃	1200	V
V_{GES}	Gate-Emitter Voltage		±20	V
I_C	Continuous Collector Current	T_C=100℃	450	A
		T_C=25℃	735	A
I_{CM}	Peak Collector Current Repetitive	tp=1ms	900	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation (IGBT)	T_C=25℃ T_{Jmax}=175℃	2940	W

Electrical Characteristics of IGBT

Static Characteristics

Symbol	Description	Conditions		Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=18mA, V_{CE}=V_{GE}, T_J=25℃		5.2	5.8	6.6	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=450A, V_{GE}=15V	T_J=25℃		2.00	2.40	V
			T_J=125℃		2.50		V
			T_J=150℃		2.60		V
I_{CES}	Collector-Emitter Leakage Current	V_{GE}=0V, V_{CE}=V_{CES}, T_J=25℃				1	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=±20V, V_{CE} =0V, T_J=25℃				800	nA
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =100kHz, T_J=25℃			40.0		nF
C_{oes}	Output Capacitance				2.2		nF
C_{res}	Reverse Transfer Capacitance				1.1		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	V_{CC}=600V,I_C=450A, R_{Gon} =1Ω,V_{GE}=±15V, Inductive Load	T_J=25℃		0.48		μs
			T_J=125℃		0.48		
			T_J=150℃		0.48		
t_r	Rise Time		T_J=25℃		0.13		μs
			T_J=125℃		0.14		
			T_J=150℃		0.14		
$t_{d(off)}$	Turn-off Delay Time	V_{CC}=600V,I_C=450A, R_{Goff} =1Ω,V_{GE}=±15V, Inductive Load	T_J=25℃		0.33		μs
			T_J=125℃		0.33		
			T_J=150℃		0.33		
t_f	Fall Time		T_J=25℃		0.06		μs
			T_J=125℃		0.07		
			T_J=150℃		0.07		
E_{on}	Turn-on Switching Loss	V_{CC}=600V,I_C=450A, R_{Gon} =1Ω,V_{GE}=±15V, di/dt=2740A/μs (T_J=150℃) Inductive Load	T_J=25℃		10.4		mJ
			T_J=125℃		17.7		
			T_J=150℃		19.0		

E_{off}	Turn-off Switching Loss	V_{CC}=600V,I_C=450A, R_{Goff}=1Ω,V_{GE}= ±15V, du/dt=6630V/μs (T_J=150℃) Inductive Load	T_J=25℃		33.2		mJ
			T_J=125℃		43.8		
			T_J=150℃		46.0		
Q_g	Total Gate Charge	V_{GE}=+15V…-15V	T_J=25℃		1.92		uC
$R_{g\ internal}$	Internal Gate Resistance		T_J=25℃		1.67		Ω
RBSOA	I_C=900A,V_{CC}=1050V,Vp=1200V, R_{Goff} = 1Ω, V_{GE}=+15V to 0V, T_J=150°C			Trapezoid			
SCSOA	V_{CC}=600V, V_{GE}=15V, T_J=150℃			10			us
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case(per leg)					0.051	℃/W

Diode, Inverter
Maximum Rated Values of Diode

V_{RRM}	Repetitive Peak Reverse Voltage	T_J=25℃	1200	V
I_F	Diode Continuous Forward Current		450	A
I_{FM}	Diode Maximum Forward Current	tp=1ms	900	A

Electrical Characteristics of Diode

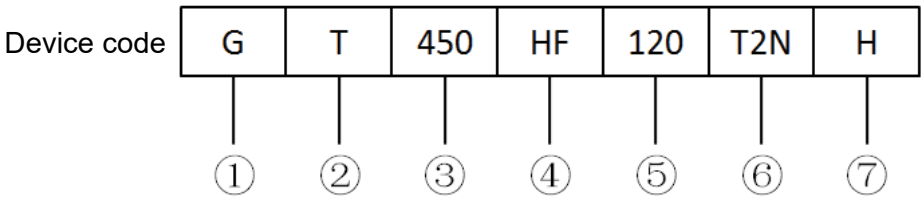
Symbol	Description	Conditions		Min	Typ	Max	Unit
V_{FM}	Forward Voltage	I_F=450A	T_J=25℃		1.90	2.30	V
			T_J=125℃		2.10		
			T_J=150℃		2.10		
t_{rr}	Reverse Recovery Time	I_F=450A, -diF/dt=3435A/μs(T_J=150℃), V_R=600V, V_{GE}=-15V	T_J=25℃		0.25		μs
			T_J=125℃		0.49		
			T_J=150℃		0.51		
I_{rr}	Peak Reverse Recovery Current		T_J=25℃		230		A
			T_J=125℃		281		
			T_J=150℃		305		

Q_{rr}	Reverse Recovery Charge	I_F=450A, -diF/dt=3435A/μs(T_J=150℃), V_R=600V, V_{GE}=-15V	T_J=25℃		31.8		μC
			T_J=125℃		59.7		
			T_J=150℃		67.5		
E_{rec}	Reverse Recovery Energy		T_J=25℃		15.6		mJ
			T_J=125℃		31.0		
			T_J=150℃		35.5		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case (per leg)					0.111	℃/W

Module

Symbol	Description		Min	Typ	Max	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted)	f = 50Hz, 1minute	2500			V
Material of Module Baseplate			Copper			
Internal Isolation			Al2O3			
L_{SCE}	Stray Inductance Module			14		nH
T_J	Maximum Junction Temperature				175	℃
T_{JOP}	Maximum Operating Junction Temperature Range		-40		+150	℃
T_{stg}	Storage Temperature		-40		+125	℃
CTI	Comparative Tracking Index		200			
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)				0.03	℃/W
T	Power Terminals Screw:M6		3.0		5.0	N·m
T	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			300		g

Ordering Information Table



① - IGBT Module
② - Trench & Field Stop IGBT
③ - Rated Current (450=450A)
④ - Circuit Configuration: HF(Half Bridge)/CE(Common Emitter)
⑤ - Rated Voltage (120=1200V)
⑥ - Package Type
⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)

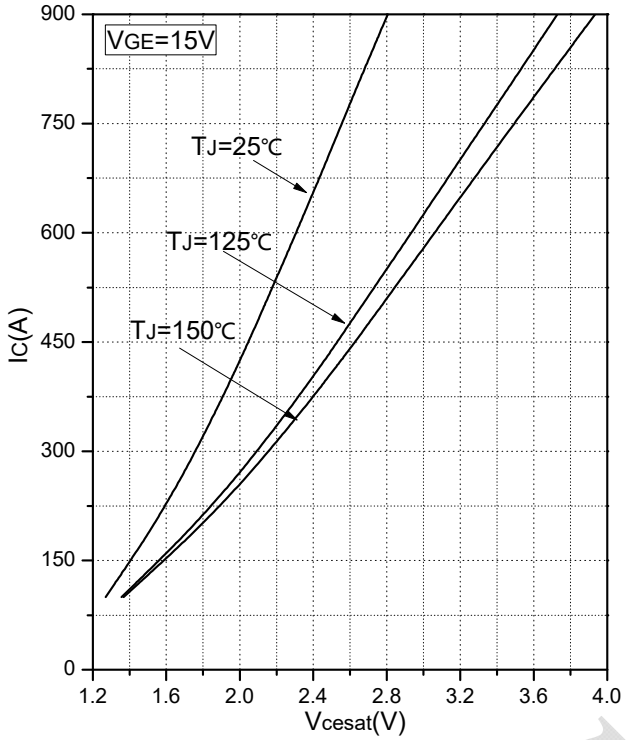


Fig.1 Typical Saturation Voltage Characteristics

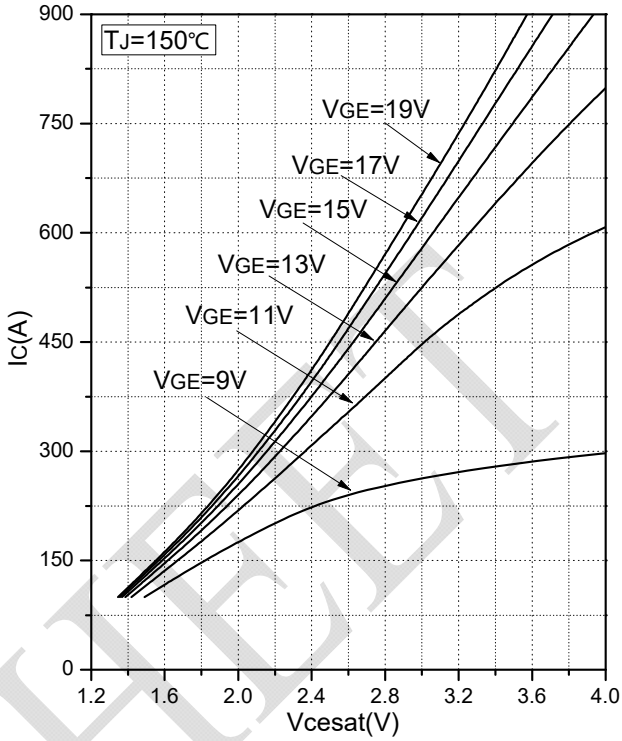


Fig.2 Typical Output Characteristics

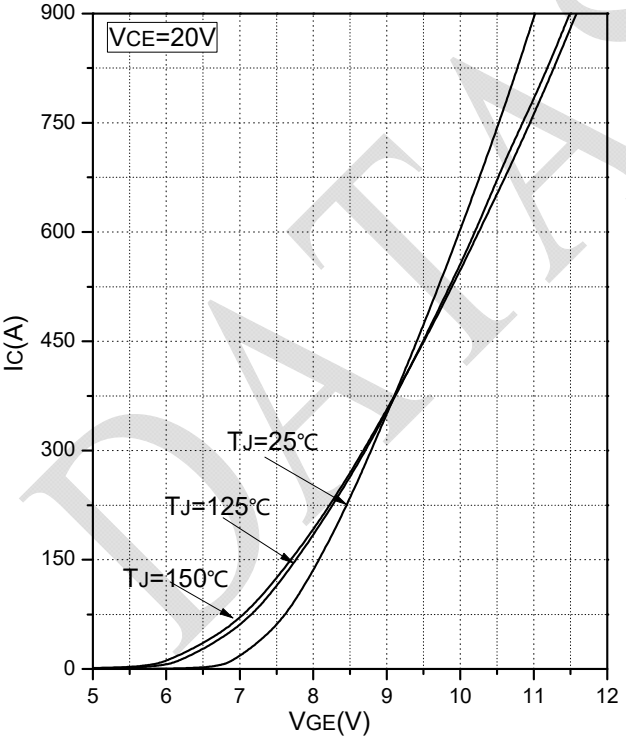


Fig.3 Transfer Characteristic

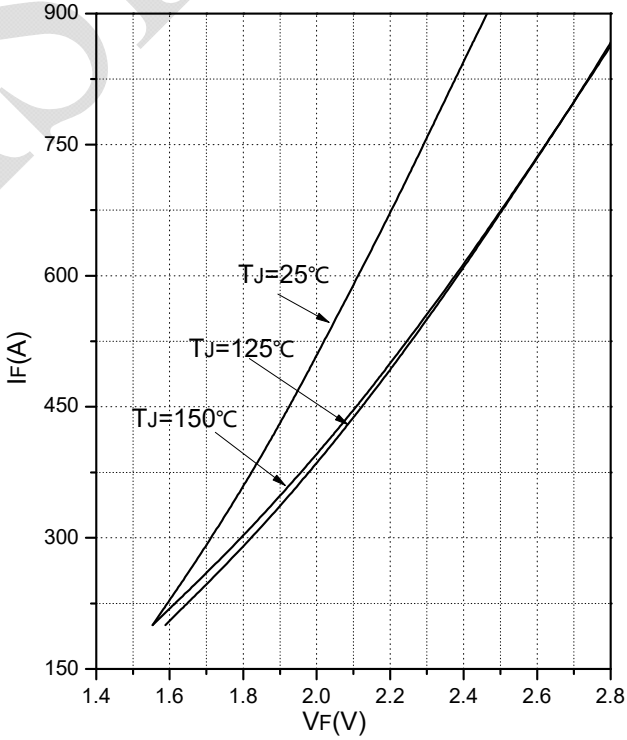


Fig.4 Forward Characteristics of Diode

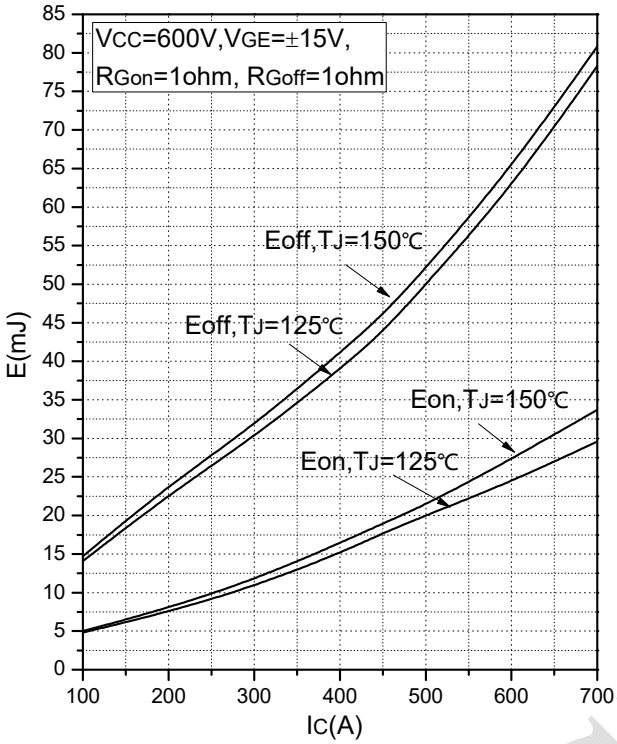


Fig.5 Typical Switching Loss vs. Collector Current

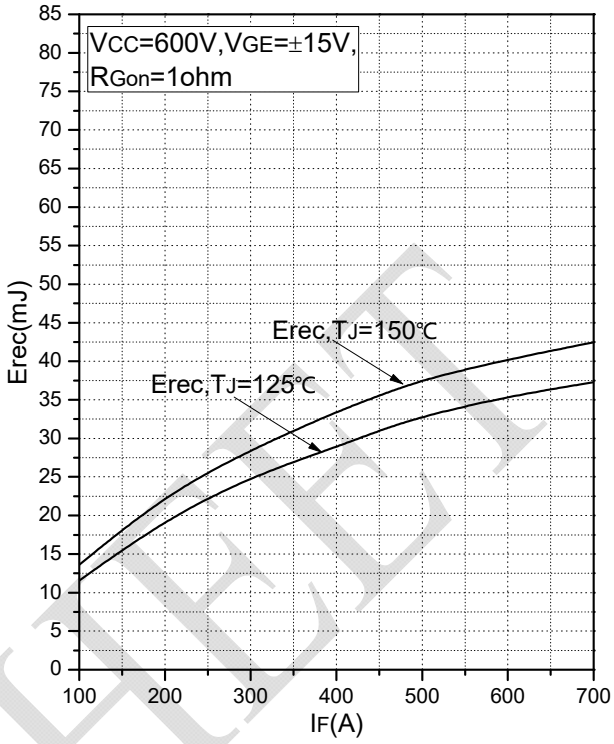


Fig.6 Typical Switching Loss vs. Forward Current

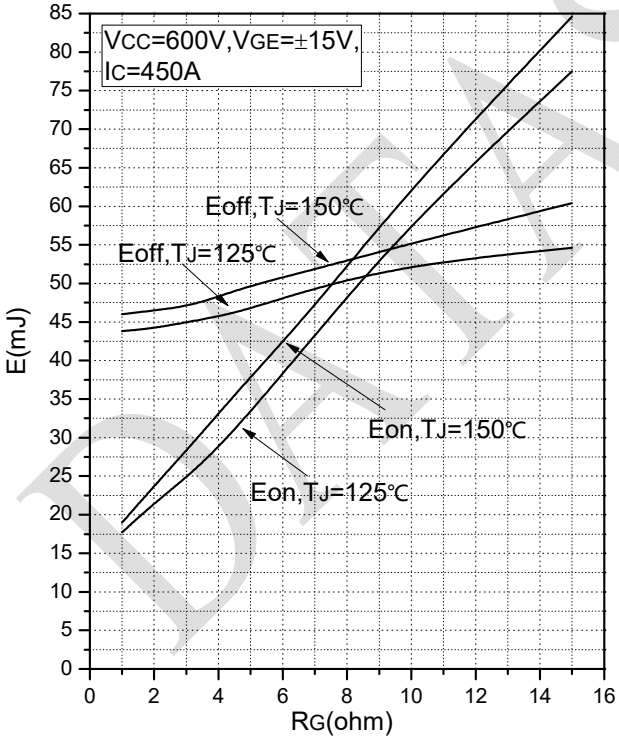


Fig.7 Typical Switching Loss vs. Gate Resistance

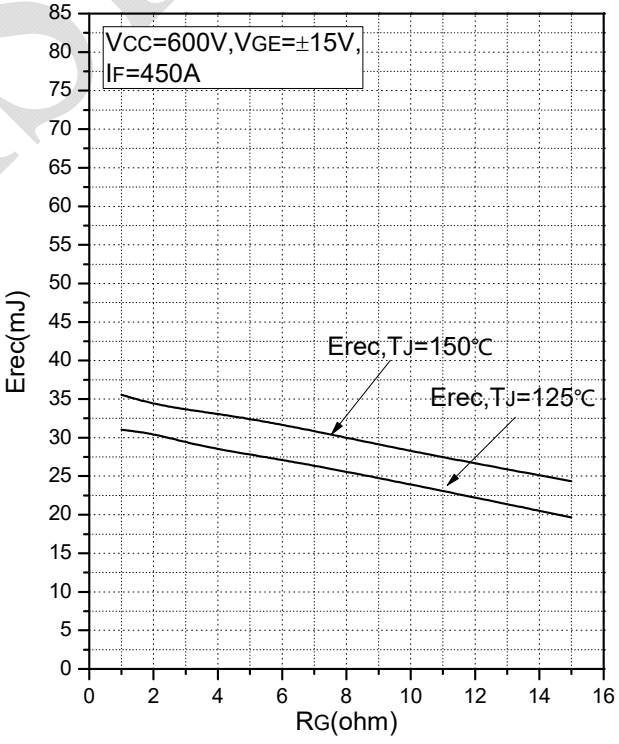


Fig.8 Typical Switching Loss vs. Gate Resistance

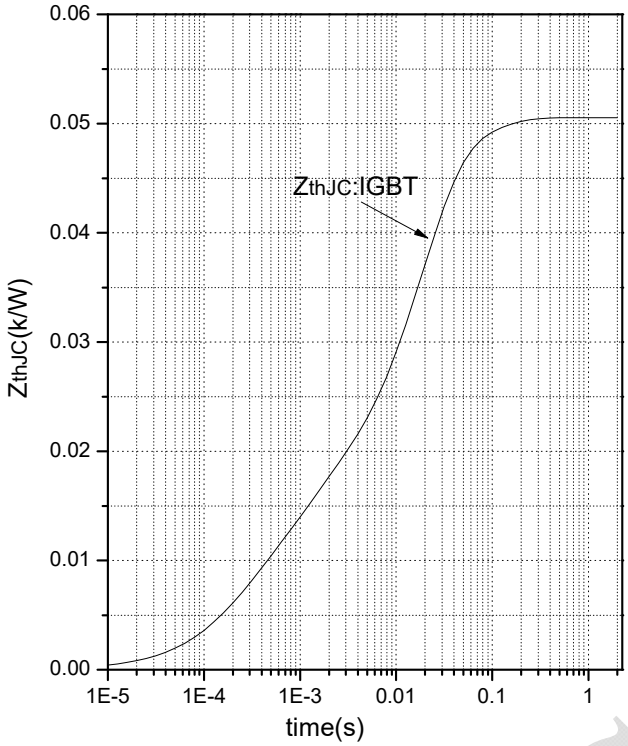


Fig.9 Transient Thermal Impedance (IGBT)

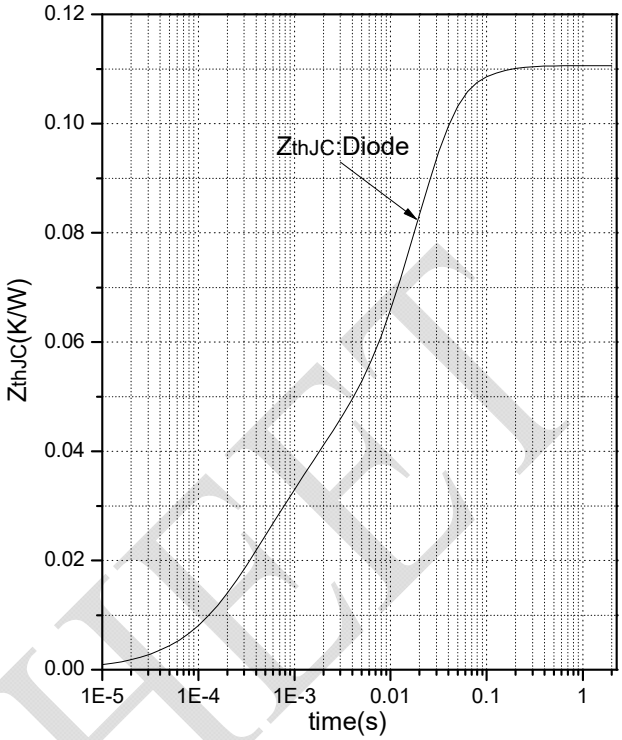


Fig.10 Transient Thermal Impedance (Diode)

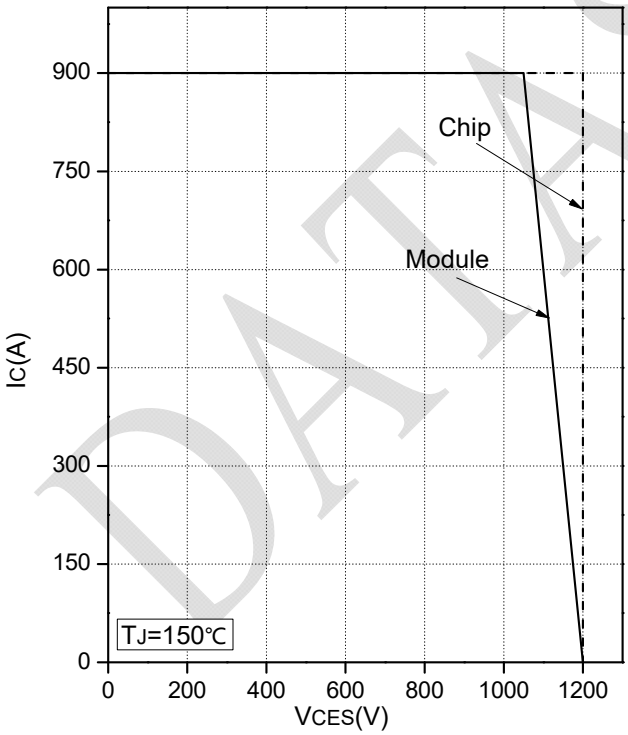
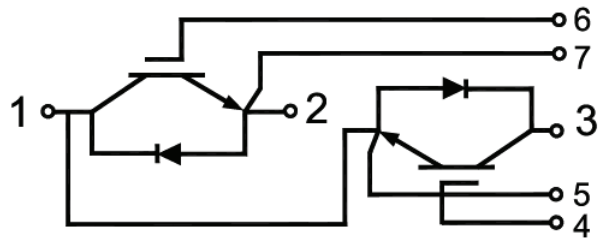
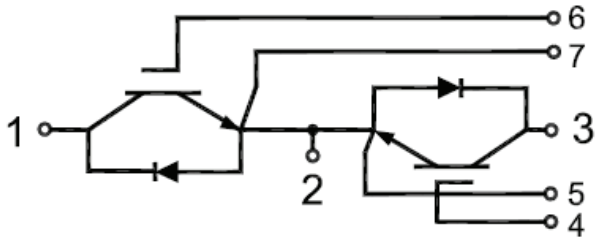


Fig.11 Reverse Bias Safe Operation Area (RBSOA)

Internal Circuit:

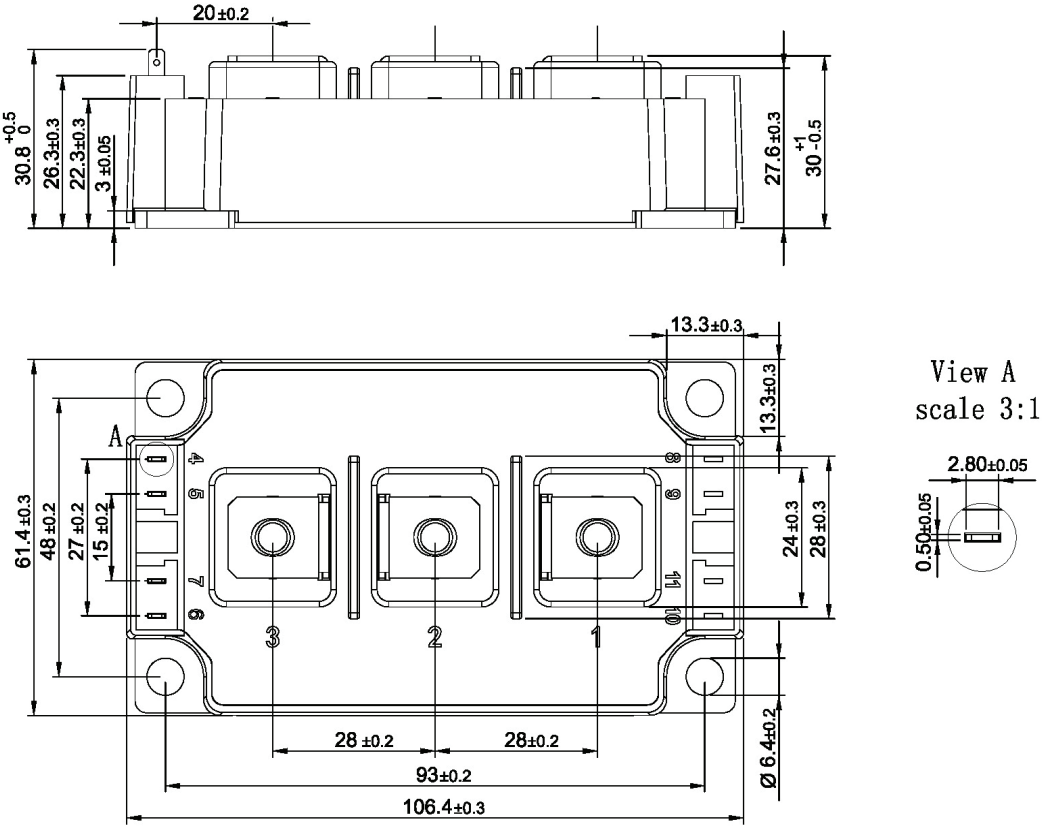


HF



CE

Package Outline (Unit: mm):



Date	Revision	Notes
06/23/2022	A	Final Version

Announcement

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